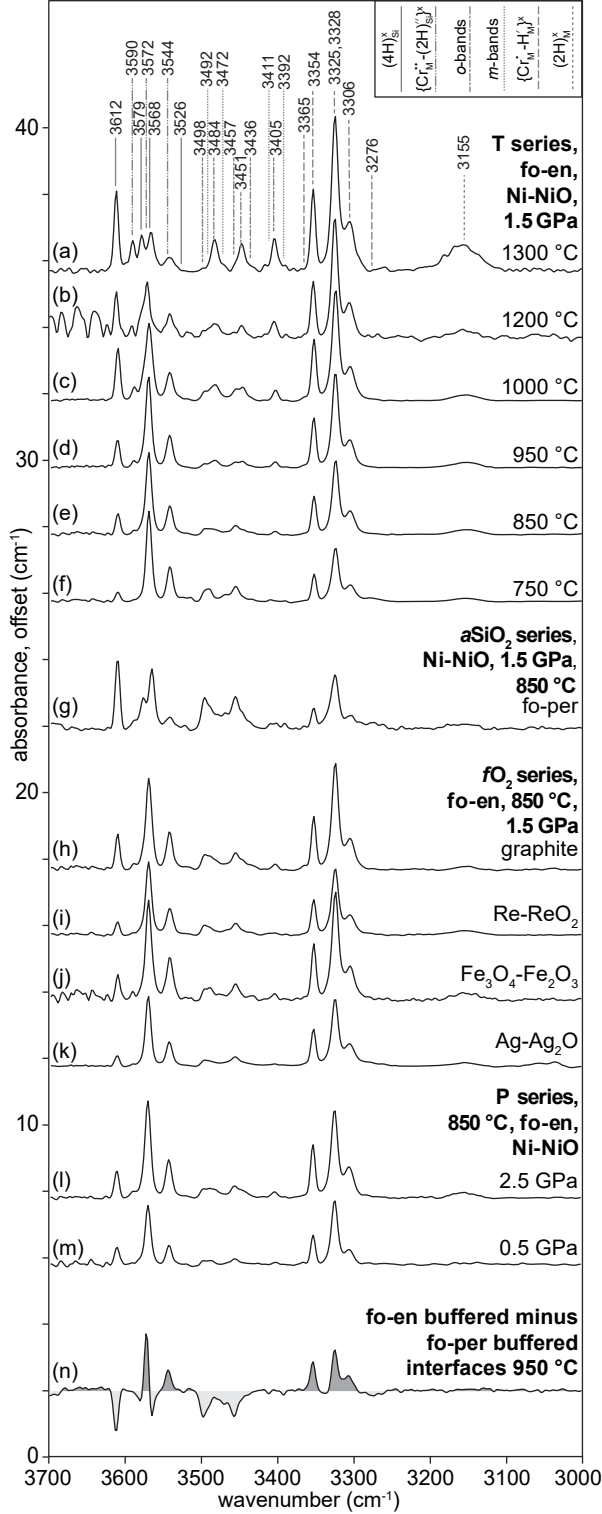
(4H)$^x_{Si}$
{$Cr^{\cdot\cdot}_M$-(2H)$^{\cdot/x}_{Si}$}^{x}
o-bands
m-bands
{$Cr^{\cdot}_M$-H_i}^{x}
(2H)^x_M
3612
3590
3579
3572
3568
3544
3526
3498
3492
3484
3472
3457
3451
3436
3411
3405
3392
3365
3354
3325, 3328
3306
3276
3155
T series, fo-en, Ni-NiO, 1.5 GPa
(a) 1300 °C
(b) 1200 °C
(c) 1000 °C
(d) 950 °C
(e) 850 °C
(f) 750 °C
aSiO2 series, Ni-NiO, 1.5 GPa, 850 °C
(g) fo-per
fO2 series, fo-en, 850 °C, 1.5 GPa
(h) graphite
(i) Re-ReO2
(j) Fe3O4-Fe2O3
(k) Ag-Ag2O
P series, 850 °C, fo-en, Ni-NiO
(l) 2.5 GPa
(m) 0.5 GPa
fo-en buffered minus fo-per buffered interfaces 950 °C
(n)
absorbance, offset (cm-1)
0
10
20
30
40
3700
3600
3500
3400
3300
3200
3100
3000
wavenumber (cm-1)